NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE3401A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

• $V_{DS} = -30V, I_{D} = -4.4A$

 $R_{DS(ON)}$ < 85m Ω @ V_{GS} =-2.5V

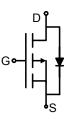
 $R_{DS(ON)}$ < 65m Ω @ V_{GS} =-4.5V

 $R_{DS(ON)}$ < 52m Ω @ V_{GS} =-10V

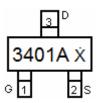
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT-23 top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3401A X	NCE3401A	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous	I _D	-4.4	Α
Drain Current-Pulsed (Note 1)	I _{DM}	-30	Α
Maximum Power Dissipation	P _D	1.3	W
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	$^{\circ}\!$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	95	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V



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I _{DSS}	V _{DS} =-30V,V _{GS} =0V	-	-	-1	μA	
I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)						
V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-0.6	-1	-1.3	V	
	V _{GS} =-10V, I _D =-4.4A	-	42	52	mΩ	
ce R _{DS(ON)}	V _{GS} =-4.5V, I _D =-4A	-	48	65	mΩ	
	V _{GS} =-2.5V, I _D =-2A		68	85	mΩ	
g FS	V _{DS} =-5V,I _D =-1A	-	10	-	S	
			•			
C _{lss}	\/ - 45\/\/ -0\/	-	950	-	PF	
C _{oss}		-	115	-	PF	
C _{rss}	F-1.UWIHZ	-	75	-	PF	
t _{d(on)}		-	7	-	nS	
t _r	V _{DD} =-15V,I _D =-4A	-	3	-	nS	
t _{d(off)}	V_{GS} =-10 V , R_{GEN} =6 Ω	-	30	-	nS	
t _f		-	12	-	nS	
Qg		-	9.5	-	nC	
Q _{gs}	V _{DS} =-15V,I _D =-4A,V _{GS} =-4.5V	-	2	-	nC	
Q_{gd}		-	3	-	nC	
Drain-Source Diode Characteristics						
V _{SD}	V _{GS} =0V,I _S =-4.4A	-	-	-1.2	V	
	IGSS	$I_{GSS} \qquad V_{GS} = \pm 12 V, V_{DS} = 0 V$ $V_{GS}(th) \qquad V_{DS} = V_{GS}, I_D = -250 \mu A$ $V_{GS} = -10 V, I_D = -4.4 A$ $V_{GS} = -2.5 V, I_D = -2A$ $V_{DS} = -5 V, I_D = -1A$ $C_{ISS} \qquad V_{DS} = -5 V, V_{GS} = 0 V,$ $C_{OSS} \qquad F = 1.0 MHz$ $t_{d(on)} \qquad t_r \qquad V_{DD} = -15 V, I_D = -4A$ $V_{GS} = -10 V, R_{GEN} = 6\Omega$ $t_f \qquad Q_g$ $Q_{gS} \qquad V_{DS} = -15 V, I_D = -4A, V_{GS} = -4.5 V$ $Q_{gd} \qquad V_{DS} = -15 V, I_D = -4A, V_{GS} = -4.5 V$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	

Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature}.$
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- **4.** Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

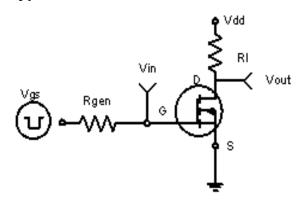


Figure 1:Switching Test Circuit

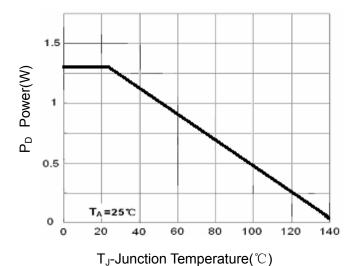


Figure 3 Power Dissipation

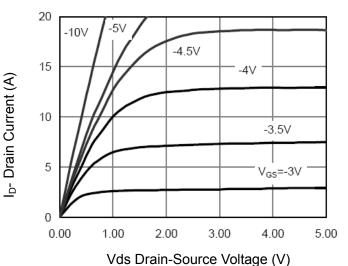


Figure 5 Output Characteristics

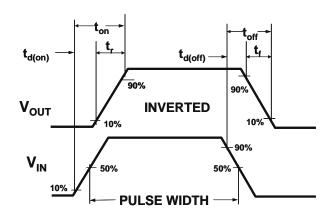


Figure 2:Switching Waveforms

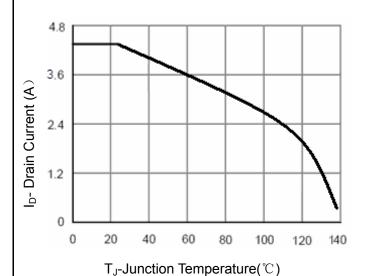


Figure 4 Drain Current

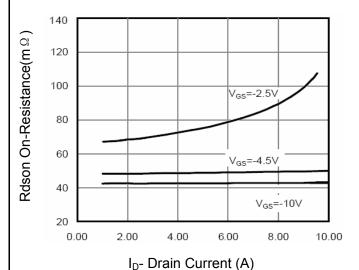


Figure 6 Drain-Source On-Resistance



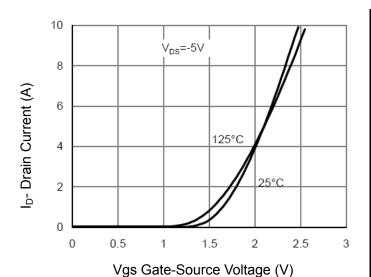
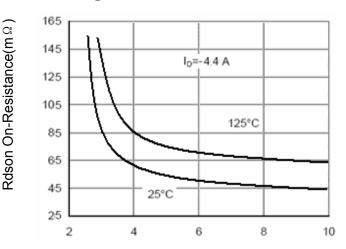


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V) Figure 9 Rdson vs Vgs

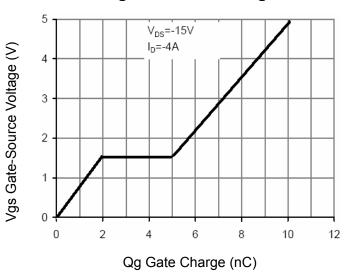
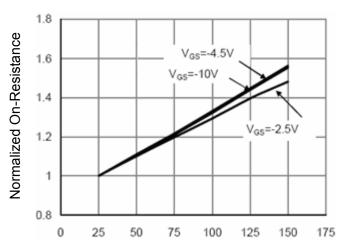


Figure 11 Gate Charge



 T_J -Junction Temperature($^{\circ}$ C) Figure 8 Drain-Source On-Resistance

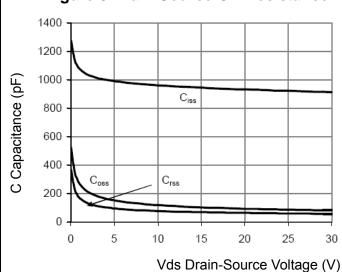


Figure 10 Capacitance vs Vds

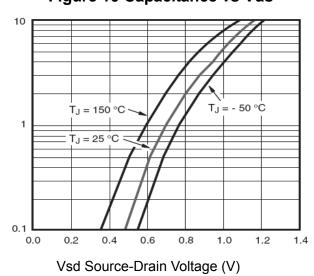


Figure 12 Source- Drain Diode Forward

Is- Reverse Drain Current (A)



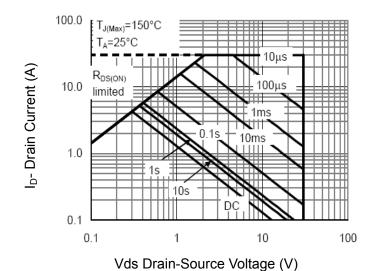


Figure 13 Safe Operation Area

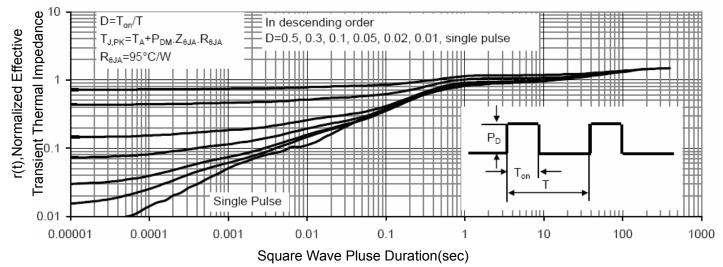
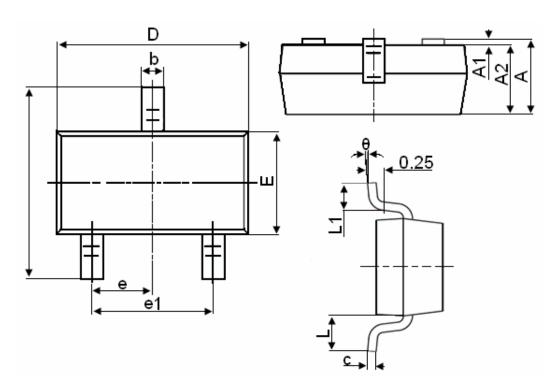


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Information



Symbol	Dimensions in Millimeters				
Symbol	MIN.	MAX.			
Α	0.900	1.150			
A1	0.000	0.100			
A2	0.900	1.050			
b	0.300	0.500			
С	0.080	0.150			
D	2.800	3.000			
Е	1.200	1.400			
E1	2.250	2.550			
е		0.950TYP			
e1	1.800	2.000			
L	0.550REF				
L1	0.300	0.500			
θ	0°	8°			

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
 - 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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